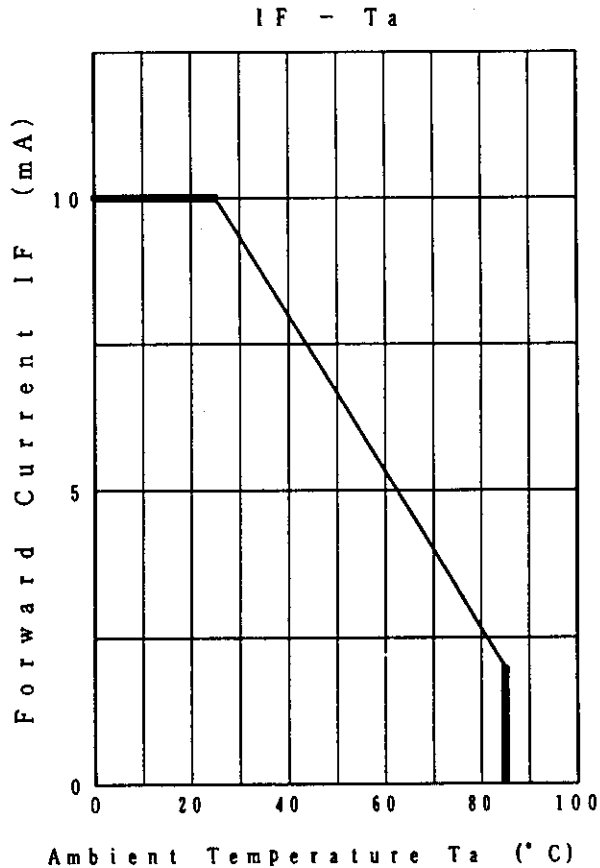
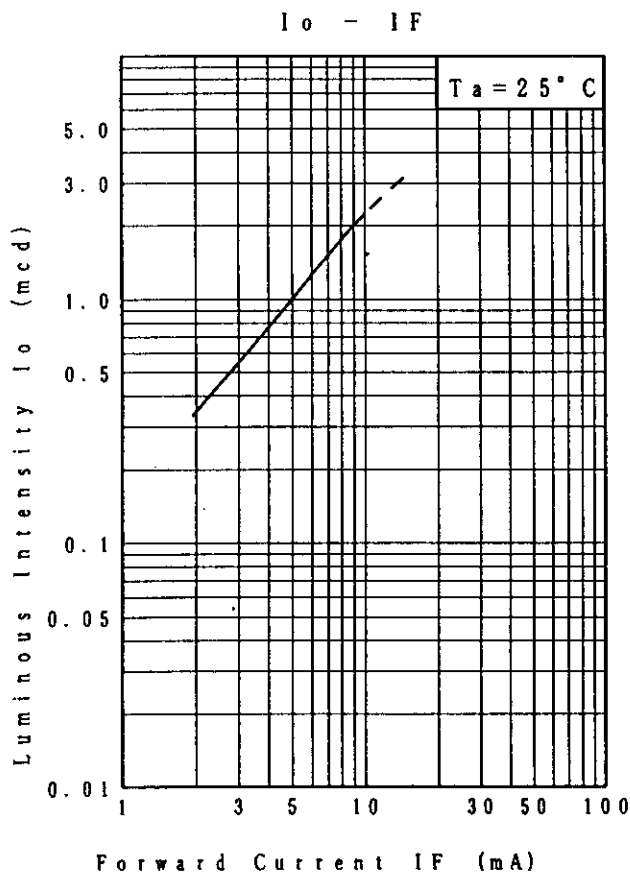
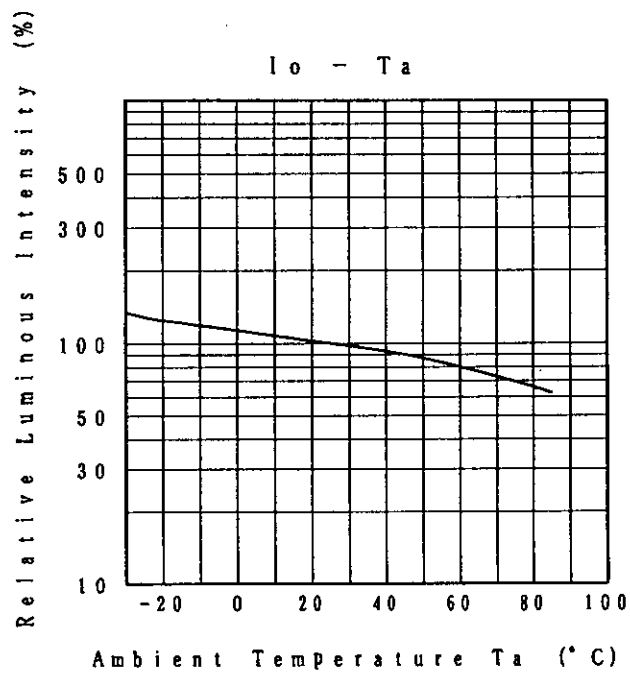
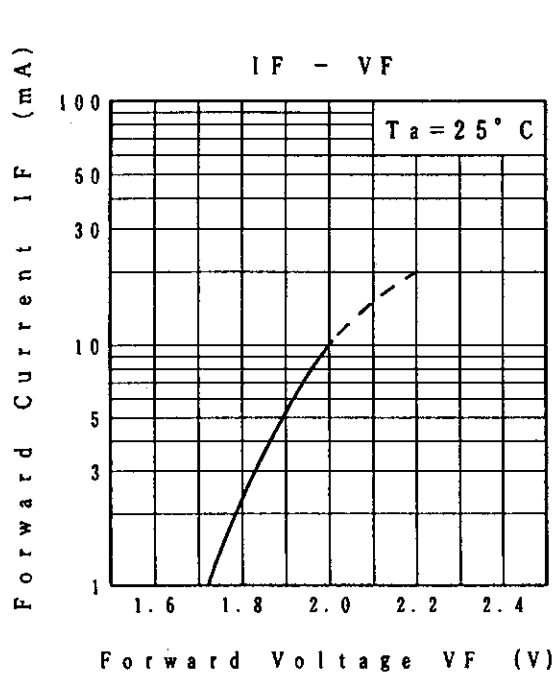


Approved <i>M. Yamashita</i>	Checked <i>M. Kikuchi</i>	Designed <i>T. Takata</i>	DEVELOPMENT SPECIFICATION P/N: LN1471SYTRP					
T Y P E			Amber Light Emitting Diode					
APPLICATION			Indicators					
MATERIAL			GaAsP					
OUTLINE			Attached					
ABSOLUTE MAXIMUM RATINGS			P 30 mW	※IFP 50 mA	IFDC 10 mA	VR 4 V	Topr -30~+85 ℃	Tstg -40~+100 ℃
CONDITION			Ta=25±3 ℃					
Test Specification								
Item	Symbol	Condition	Typ	Limit		Unit		
				Min	Max			
Forward Voltage	VF	IF= 5 mA	1.9		2.4	V		
Reverse Leakage Current	IR	VR= 4 V			10	μA		
Luminous Intensity	IO	IF= 5 mA · DC	1.0	0.4		mcd		
Peak Emission Wavelength	λp	IF= 5 mA · DC	590			nm		
Spectral Line Half Width	Δλ	IF= 5 mA · DC	30			nm		
※ · The condition of IFP is duty 10 % , Pulse width 1 ms · Please contact the Panasonic local office if you design at low current (below 0.5 mA DC) or pulse current operation and have any questions. NOTE ★1 Soldering conditions. Refer to handling note. ★2 Care should be taken that soldering is done within 3-days after opening the dry package and reel. ★3 Package:Light yellow diffusion type. ★4 Tone of Color is passed over.								
Jun.13.1995								

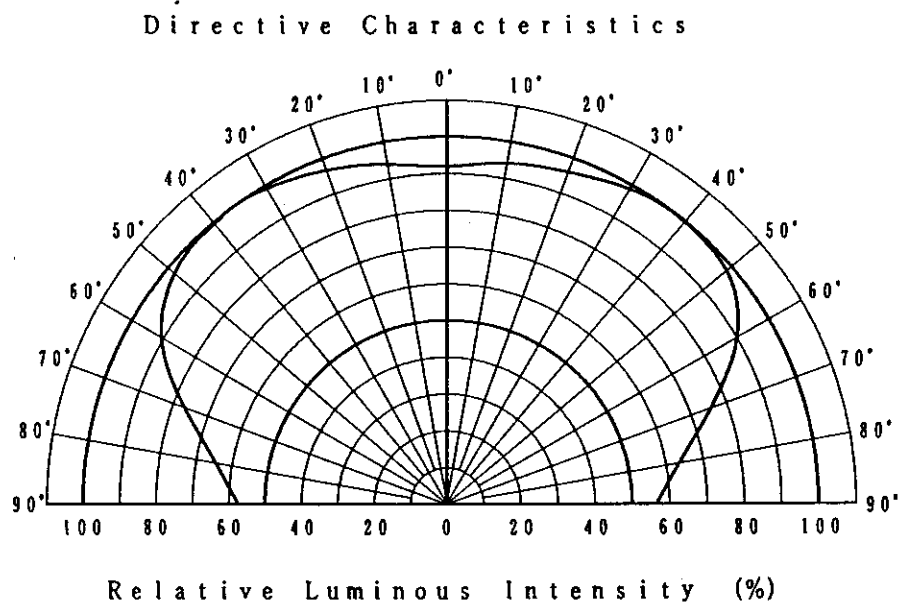
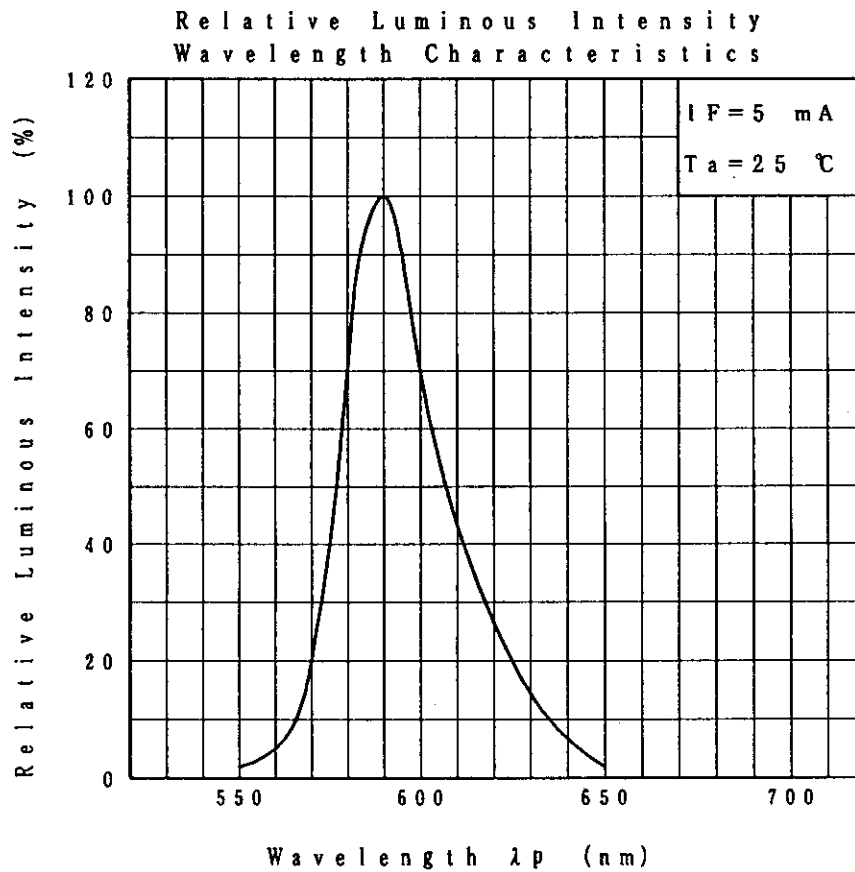
Approved	Checked	Designed	DEVELOPMENT SPECIFICATION		
<i>N. Kuroki</i>	<i>K. Kikuchi</i>	<i>T. Taira</i>	P/N: LN1471SYTRP		



Approved	Checked	Designed
<i>[Signature]</i>	<i>[Signature]</i>	<i>[Signature]</i>

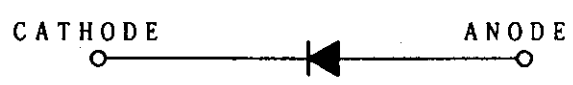
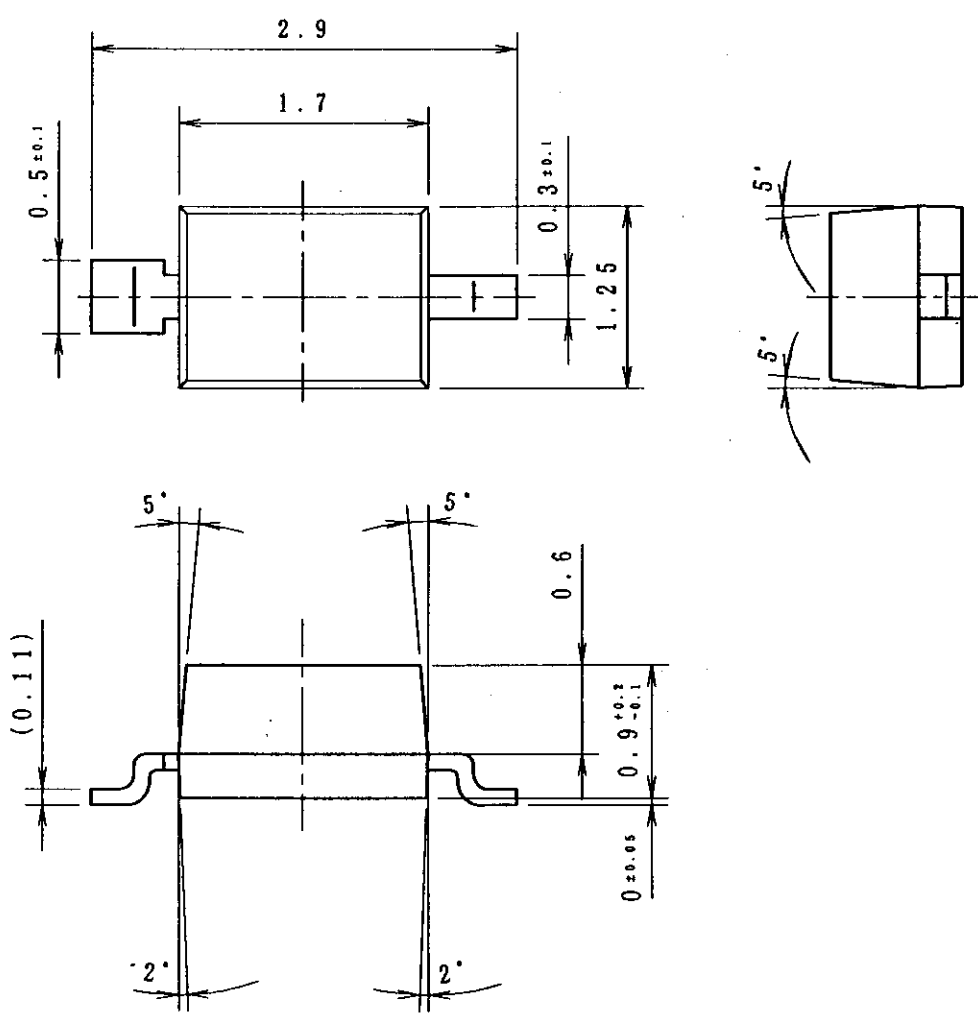
DEVELOPMENT SPECIFICATION

P/N: LN1471SYTRP



Jun. 13. 1995

Approved	Checked	Designed	DEVELOPMENT SPECIFICATION			
<i>H. Yamashita</i>	<i>K. Kikuchi</i>	<i>T. Takata</i>				
			PN: LN1471SYTRP			



- (NOTE)
1. Unit:mm
 2. Tolerance unless specified is ± 0.2 .
 3. Measurement of the package doesn't include gate projection.
 4. Corner of the package is R 0.2max.
 5. Projection's tolerance of the package is 0.2max.

Jun. 13. 1995			